	TVD	Hite	F 1-10	
	7 7 7		Search I Xt	DBs
	BRS	90479	image near2 sens\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
တ	BRS	51	(image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	2768	(deep near2 well).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
-	BRS	8	(image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well).ab.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	BRS	150454	54 inplant or implant or inplanting or implanting	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
<u>n</u>	BRS	874	(second! or another or additional\$4 or deep\$4) near4 (inplant or implant or inplanting or implanting) near4 well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	200
4	BRS	22	(image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and ((second! or another or additional\$4 or deep\$4) near4 (inplant or implant or inplanting or implanting) near4 well)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	4	((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and ((second! or another or additional\$4 or deep\$4) near4 (inplant or implant or inplanting or implanting) near4 well)) not (((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (@ad < "20031710"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	BRS	_	lixin-zhao.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	BRS	2	6586789.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	BRS	4	("5416345" "5898195" "5904493" "6051447").PN.	USPAT
19	BRS	0	6586789.URPN.	USPAT

	Type	Hits	Search Toxt	
20	BRS	25	well near4 (micron or mu)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
21	BRS	16	(image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (well near4 (micron or mu))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
22	BRS	2	20020036303.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
23	BRS	_	20020036303.pn. and bias\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
24	BRS	41462	n near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
25	BRS	7071	p near2 (epi or epitax\$8)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
26	BRS	33799	n near2 well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

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27.	BRS	88761	photodiode or photo adj diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB
28	BRS	90479	image near2 sens\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
29	BRS	186229	mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
30	BRS	88	(n near2 substrate) and (p near2 (epi or epitax\$8)) and (n near2 well) and (photodiode USPAT; or photo adj diode) and (image near2 sens\$4 US-PGPUB; EPO;) and (mosfet or (metal adj oxide adj Semiconducor adj (fet or field)) or pmos or lBM_TDB cmos or misfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
Ξ	BRS	38	((n near2 substrate) and (p near2 (epi or epitax\$8)) and (n near2 well) and (photodiode USPAT; or photo adj diode) and (image near2 sens\$4 US-PGPUB; EPO; and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or mos or misfet)) and (@ad < IBM_TDB "20031710")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
22	BRS	90479	(image near2 sens\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

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	Тур	Hits	S arch T xt	DBs
33	BRS	2903	((image near2 sens\$4)) near2 cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
34	BRS	т	(n near2 substrate) same (p near2 (epi or epitax\$8)) same (n near2 well) same (photodiode or photo adj diode) and (@ad < "20031710")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
35	BRS	88761	photodiode or photo adj diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
36	BRS	11752	deep near2 well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
37	BRS	13	((((image near2 sens\$4)) near2 cmos) same (photodiode or photo adj diode)) and (deep near2 well)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
38	BRS	569		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
39	BRS	51	((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (@ad < "20031710")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

467622 cmp or planar\$4 (((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (@ad < "20031710") and (cmp or planar\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (@ad < "20031710") (cmp or planar\$4) and (((image near2 sens\$4) and (mosfet or field)) or pmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 sens\$4) and (deep near2 well)) and (@ad < "20031710") (image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (photodiode or photo adj diode) and (deep near2 well)) and (photodiode or photo adj diode) and (deep near2 well)) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (@ad < "20031710")	Type	Hits	Search Text) DB.
(((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (@ad < "20031710") and (cmp or planar\$4) ((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (@ad < "20031710") (cmp or planar\$4) and (((image near2 sens\$4) and (mosfet or (metal adj oxide adj) semiconducor adj (fet or field)) or pmos or cmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (@ad < "20031710") (image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (@ad < "20031710") 556110 cmp or planariz\$4	BRS		cmp or planar\$4	USPAT; US-PGPUB; EPO JPO; DERWENT; IBM_TDB
((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (@ad < "20031710") (cmp or planar\$4) and ((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (@ad < "20031710") (image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (@ad < "20031710") 56110 cmp or planariz\$4	BRS		(((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (@ad < "20031710")) and (cmp or planar\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
(cmp or planar\$4) and ((image near2 sens\$4) and (mosfet or (metal adj oxide adj sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or photo adj diode) and (deep near2 well) and (@ad < "20031710")) (image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (@ad < "20031710") 56110 cmp or planariz\$4	BRS		((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (@ad < "20031710")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
(image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) 2593 or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (@ad < "20031710") 56110 cmp or planariz\$4	BRS	15	(cmp or planar\$4) and (((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (@ad < "20031710"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
56110 cmp or planariz\$4		2593	(image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (@ad < "20031710")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	BRS		cmp or planariz\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

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46	 		nosfet or (metal dj (fet or field)) misfet) and (@ad <) nariz\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
47	BRS	148	r (metal field)) nd @ad <) not e adj s or s or ode or) and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
48	IS&R	1557	((438/73) or (438/75) or (438/76) or (438/200)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

90479 186229 11752 11752 11	Tvne	Hitc	Correct T v4	
186229 88761 11752 51 51	BRS	90479	image near2 sens\$4	USPAT; US-PGPUB; EPO JPO; DERWENT; IBM_TDB
88761 11752 51 51 88761	BRS		mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
51 51 88761	BRS	88761	photodiode or photo adj diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
51 51 88761	BRS		deep near2 well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
51	BRS	•	(image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
88761	BRS	51	((image near2 sens\$4) and (mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet) and (photodiode or photo adj diode) and (deep near2 well)) and (@ad < "20031710")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
	BRS		photodiode or photo adj diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB